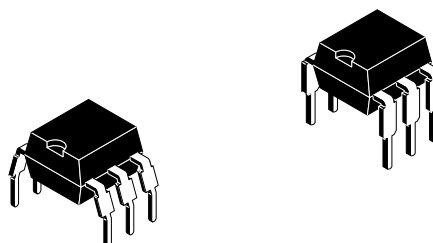


Optocoupler with Phototransistor Output

Description

The CQY80N(G) series consist of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 6-lead plastic dual in line package. The elements are mounted on one leadframe using a **coplanar technique**, providing a fixed distance between input and output for highest safety requirements.



14827

Applications

Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):

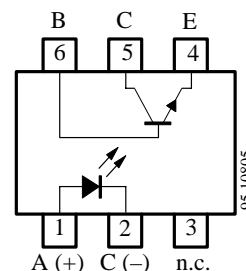
- For appl. class I – IV at mains voltage ≤ 300 V
- For appl. class I – III at mains voltage ≤ 600 V according to VDE 0884, table 2, suitable for:

Switch-mode power supplies, line receiver, computer peripheral interface, microprocessor system interface.

VDE Standards

These couplers perform safety functions according to the following equipment standards:

- **VDE 0884**
Optocoupler for electrical safety requirements
- **IEC 950/EN 60950**
Office machines (applied for reinforced isolation for mains voltage ≤ 400 V_{RMS})
- **VDE 0804**
Telecommunication apparatus and data processing
- **IEC 65**
Safety for mains-operated electronic and related household apparatus



0884

Order Instruction

Ordering Code	CTR Ranking	Remarks
CQY80N	> 50%	
CQY80NG ¹⁾	> 50%	
¹⁾ G = Leadform 10.16 mm; G is not market on the body		



Features

Approvals:

- **BSI:** BS EN 41003, BS EN 60095 (BS 415), BS EN 60950 (BS 7002), Certificate number 7081 and 7402
- **FIMKO (SETI):** EN 60950, Certificate number 12399
- **Underwriters Laboratory (UL)** 1577 recognized, file number E-76222
- **VDE 0884,** Certificate number 94778

VDE 0884 related features:

- Rated impulse voltage (transient overvoltage) $V_{IOTM} = 6$ kV peak
- Isolation test voltage (partial discharge test voltage) $V_{pd} = 1.6$ kV
- Rated isolation voltage (RMS includes DC) $V_{IOWM} = 600$ V_{RMS} (848 V peak)

- Rated recurring peak voltage (repetitive) $V_{IORM} = 600$ V_{RMS}
- Creepage current resistance according to VDE 0303/IEC 112
Comparative Tracking Index: **CTI = 275**
- Thickness through insulation ≥ 0.75 mm

General features:

- Isolation materials according to UL94-VO
- Pollution degree 2 (DIN/VDE 0110 / resp. IEC 664)
- Climatic classification 55/100/21 (IEC 68 part 1)
- Special construction: Therefore, extra low coupling capacity of typical 0.3 pF, high **Common Mode Rejection**
- Low temperature coefficient of CTR
- CTR > 50%
- Coupling System A

Absolute Maximum Ratings

Input (Emitter)

Parameter	Test Conditions	Symbol	Value	Unit
Reverse voltage		V_R	5	V
Forward current		I_F	60	mA
Forward surge current	$t_p \leq 10 \mu s$	I_{FSM}	1.5	A
Power dissipation	$T_{amb} \leq 25^\circ C$	P_V	100	mW
Junction temperature		T_j	125	$^\circ C$

Output (Detector)

Parameter	Test Conditions	Symbol	Value	Unit
Collector emitter voltage		V_{CEO}	32	V
Emitter collector voltage		V_{ECO}	7	V
Collector current		I_C	50	mA
Collector peak current	$t_p/T = 0.5, t_p \leq 10$ ms	I_{CM}	100	mA
Power dissipation	$T_{amb} \leq 25^\circ C$	P_V	150	mW
Junction temperature		T_j	125	$^\circ C$

Coupler

Parameter	Test Conditions	Symbol	Value	Unit
Isolation test voltage (RMS)	$t = 1$ min	V_{IO}	3.75	kV
Total power dissipation	$T_{amb} \leq 25^\circ C$	P_{tot}	250	mW
Ambient temperature range		T_{amb}	-55 to +100	$^\circ C$
Storage temperature range		T_{stg}	-55 to +125	$^\circ C$
Soldering temperature	2 mm from case, $t \leq 10$ s	T_{sd}	260	$^\circ C$



Electrical Characteristics ($T_{amb} = 25^{\circ}\text{C}$)

Input (Emitter)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Forward voltage	$I_F = 50 \text{ mA}$	V_F		1.25	1.6	V
Junction capacitance	$V_R = 0, f = 1 \text{ MHz}$	C_j		50		pF

Output (Detector)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Collector emitter voltage	$I_C = 1 \text{ mA}$	V_{CEO}	32			V
Emitter collector voltage	$I_E = 100 \mu\text{A}$	V_{ECO}	7			V
Collector emitter cut-off current	$V_{CE} = 20 \text{ V}, I_f = 0, E = 0$	I_{CEO}		10	200	nA

Coupler

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Collector emitter saturation voltage	$I_F = 10 \text{ mA}, I_C = 1 \text{ mA}$	V_{CEsat}			0.3	V
Cut-off frequency	$V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 100 \Omega$	f_c		110		kHz
Coupling capacitance	$f = 1 \text{ MHz}$	C_k		0.3		pF

Current Transfer Ratio (CTR)

Parameter	Test Conditions	Type	Symbol	Min.	Typ.	Max.	Unit
I_C/I_F	$V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA}$	CQY80N, CQY80NG	CTR	0.5	0.9		

Maximum Safety Ratings (according to VDE 0884) see figure 1

This device is used for protective separation against electrical shock only within the maximum safety ratings. This must be ensured by using protective circuits in the applications.

Input (Emitter)

Parameters	Test Conditions	Symbol	Value	Unit
Forward current		I_{si}	130	mA

Output (Detector)

Parameters	Test Conditions	Symbol	Value	Unit
Power dissipation	$T_{amb} \leq 25^\circ\text{C}$	P_{si}	265	mW

Coupler

Parameters	Test Conditions	Symbol	Value	Unit
Rated impulse voltage		V_{IOTM}	6	kV
Safety temperature		T_{si}	150	$^\circ\text{C}$

Insulation Rated Parameters (according to VDE 0884)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Partial discharge test voltage – Routine test	100%, $t_{test} = 1\text{ s}$	V_{pd}	1.6			kV
Partial discharge test voltage – Lot test (sample test)	$t_{Tr} = 60\text{ s}$, $t_{test} = 10\text{ s}$, (see figure 2)	V_{IOTM}	6			kV
		V_{pd}	1.3			kV
Insulation resistance	$V_{IO} = 500\text{ V}$	R_{IO}	10^{12}			Ω
	$V_{IO} = 500\text{ V}$, $T_{amb} = 100^\circ\text{C}$	R_{IO}	10^{11}			Ω
	$V_{IO} = 500\text{ V}$, $T_{amb} = 150^\circ\text{C}$ (construction test only)	R_{IO}	10^9			Ω

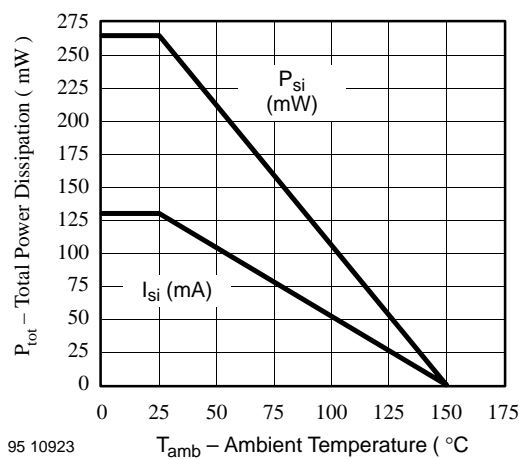


Figure 1. Derating diagram

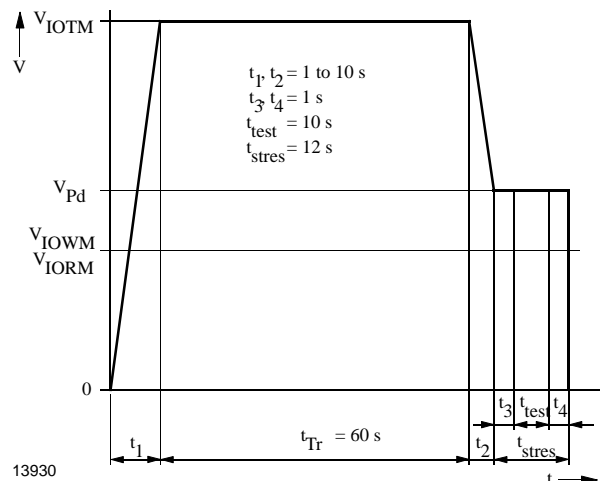


Figure 2. Test pulse diagram for sample test according to DIN VDE 0884

Switching Characteristics

Parameter	Test Conditions	Symbol	Typ.	Unit
Delay time	$V_S = 5\text{ V}$, $I_C = 5\text{ mA}$, $R_L = 100\ \Omega$ (see figure 3)	t_d	4.0	μs
Rise time		t_r	7.0	μs
Fall time		t_f	6.7	μs
Storage time		t_s	0.3	μs
Turn-on time		t_{on}	11.0	μs
Turn-off time		t_{off}	7.0	μs
Turn-on time	$V_S = 5\text{ V}$, $I_F = 10\text{ mA}$, $R_L = 1\text{ k}\Omega$ (see figure 4)	t_{on}	25.0	μs
Turn-off time		t_{off}	42.5	μs

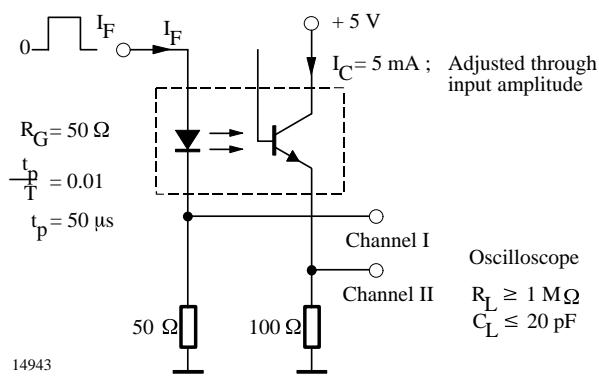


Figure 3. Test circuit, non-saturated operation

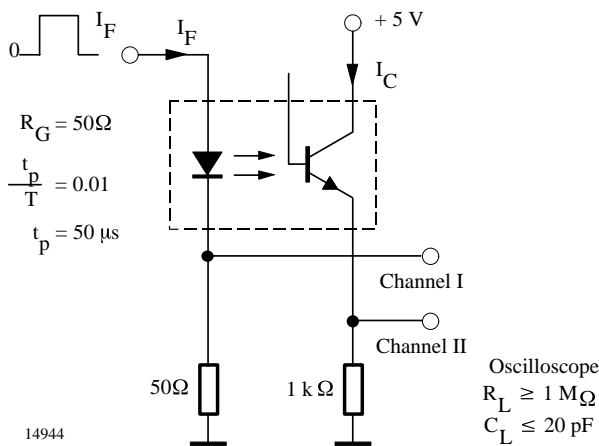
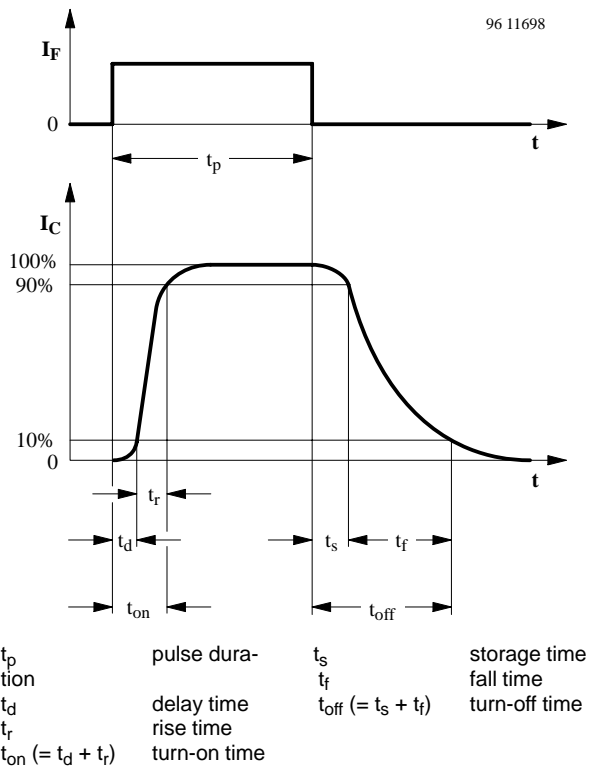
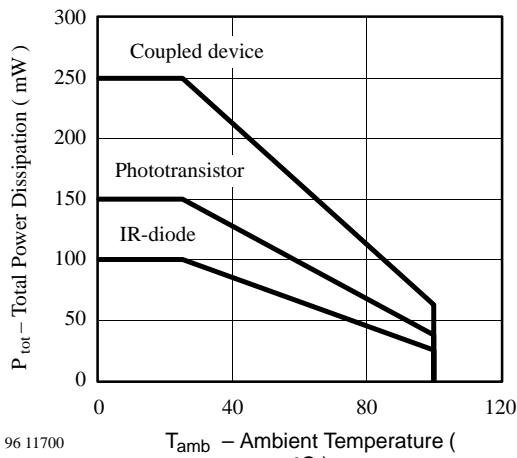


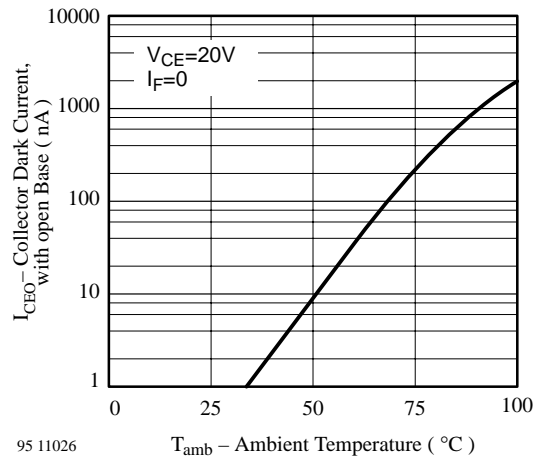
Figure 4. Test circuit, saturated operation

Figure 5. Switching times

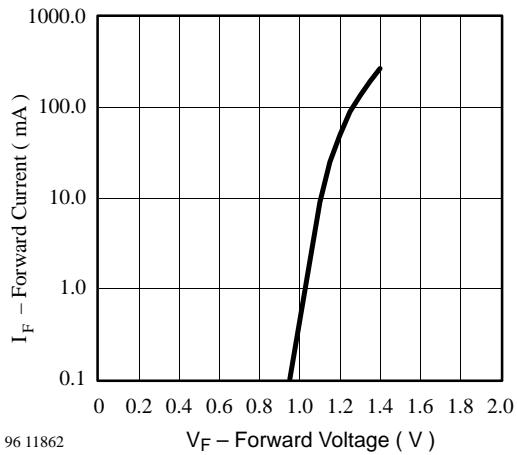
Typical Characteristics ($T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified)



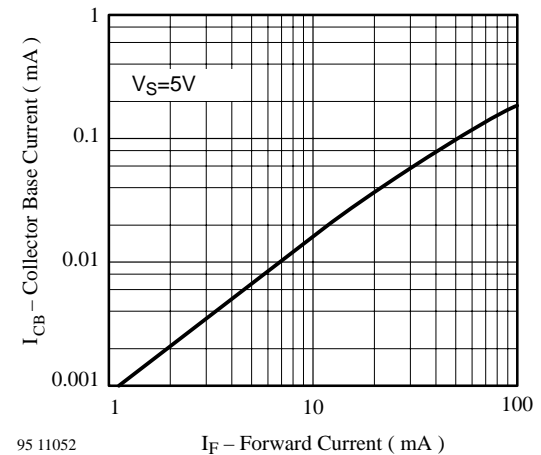
96 11700
Figure 6. Total Power Dissipation vs. Ambient Temperature



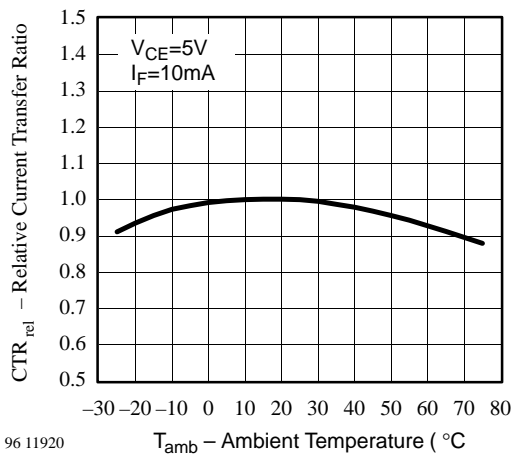
95 11026
Figure 9. Collector Dark Current vs. Ambient Temperature



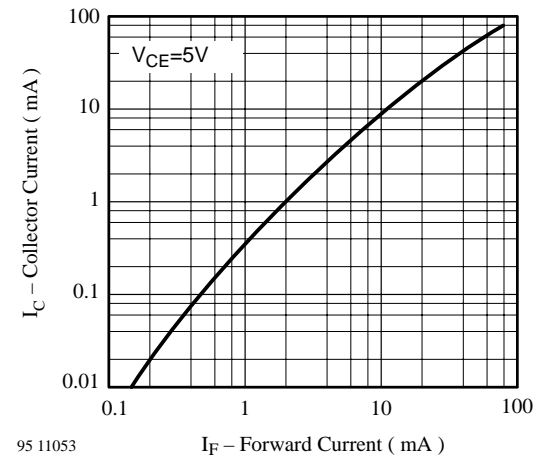
96 11862
Figure 7. Forward Current vs. Forward Voltage



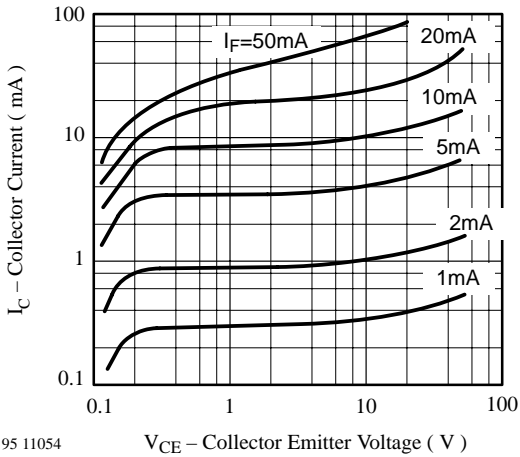
95 11052
Figure 10. Collector Base Current vs. Forward Current



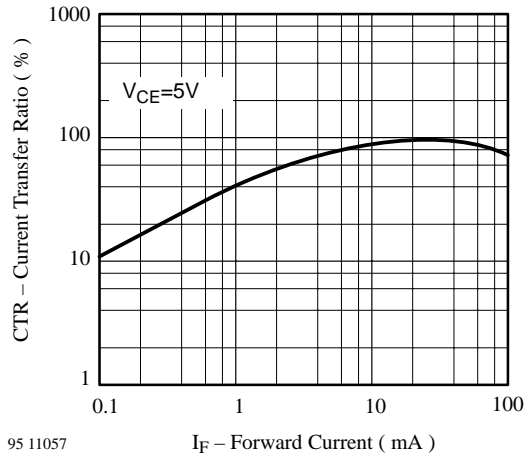
96 11920
Figure 8. Relative Current Transfer Ratio vs. Ambient Temperature



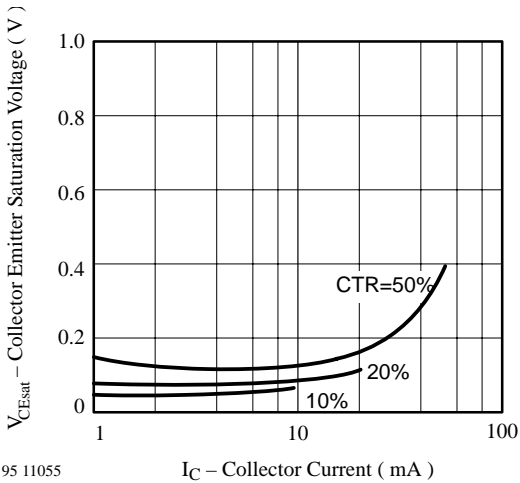
95 11053
Figure 11. Collector Current vs. Forward Current



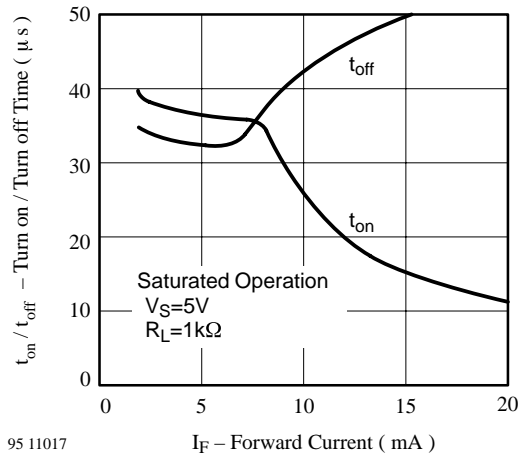
95 11054 V_{CE} – Collector Emitter Voltage (V)
 Figure 12. Collector Current vs. Collector Emitter Voltage



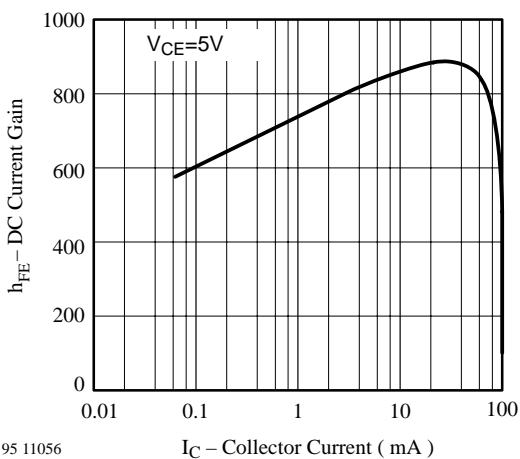
95 11057 I_F – Forward Current (mA)
 Figure 15. Current Transfer Ratio vs. Forward Current



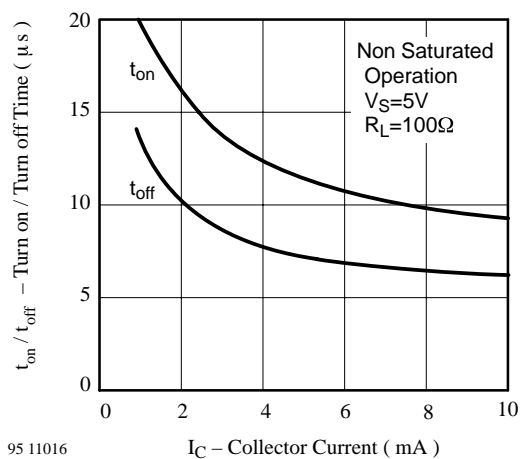
95 11055 I_C – Collector Current (mA)
 Figure 13. Collector Emitter Saturation Voltage vs. Collector Current



95 11017 I_F – Forward Current (mA)
 Figure 16. Turn on / off Time vs. Forward Current



95 11056 I_C – Collector Current (mA)
 Figure 14. DC Current Gain vs. Collector Current



95 11016 I_C – Collector Current (mA)
 Figure 17. Turn on / off Time vs. Collector Current

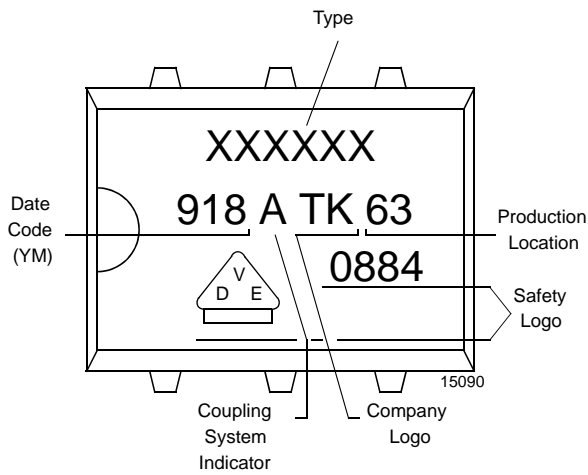
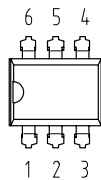
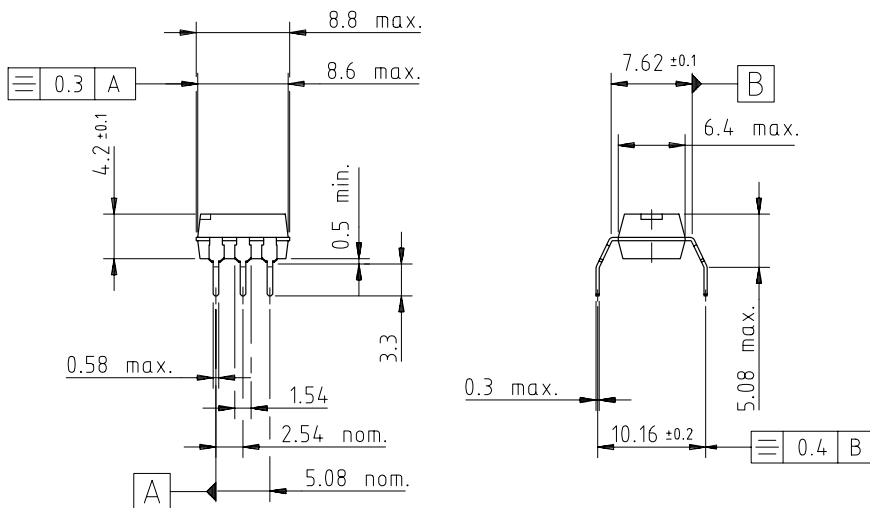


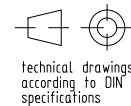
Figure 18. Marking example

Dimensions of CNY80NG in mm



weight: ca. 0.50 g
 creepage distance: ≈ 8 mm
 air path: ≥ 8 mm

after mounting on PC board



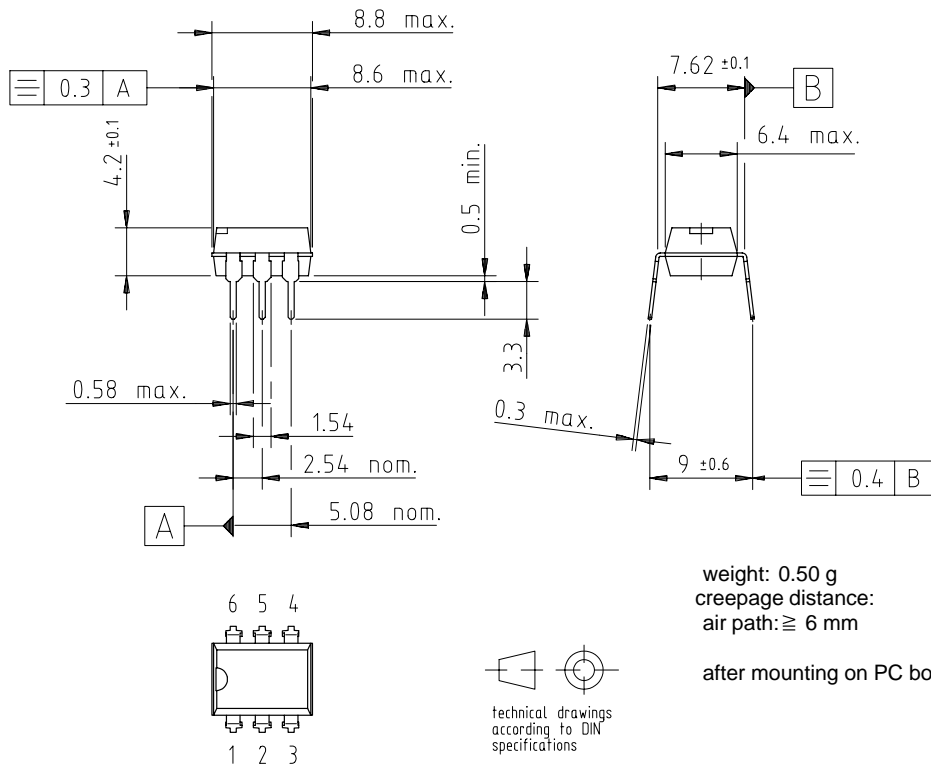
14771

CQY80N(G)

Vishay Telefunken



Dimensions of CNY80N in mm



14770



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

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- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
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- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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